

OA90
Gold Bonded Germanium Diode

FEATURES

- Low forward voltage drop—low power consumption
- Thirty years of proven reliability—one million hours mean time between failures (MTBF)
- Very low noise level
- Metallurgically bonded

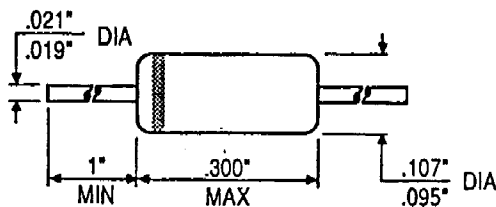
ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

Peak Inverse Voltage	30 Volts
Peak Forward Current	500 mA
Operating Temperature	- 65 °C to 85 °C
Average Power Dissipation	80 mW

ELECTRICAL CHARACTERISTICS

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	30		V	25 °C
Reverse Current	I _r	10 V		20	μA	25 °C
Forward Voltage	V _f	10 mA		1	V	25 °C

MECHANICAL



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